OSHIBA

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

SSM3J15FV

High Speed Switching Applications

Analog Switch Applications

- Optimum for high-density mounting in small packages
- Low on-resistance : $R_{on} = 12 \Omega (max) (@V_{GS} = -4 V)$: $R_{on} = 32 \Omega (max) (@V_{GS} = -2.5 V)$

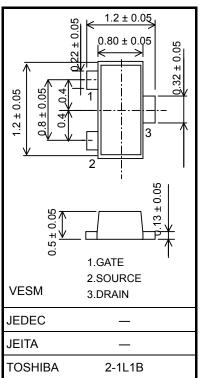
Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		V _{DS}	-30	V	
Gate-Source voltage		V _{GSS}	±20	V	
Drain current	DC	I _D	-100	mA	
	Pulse	I _{DP}	-200		
Drain power dissipation (Ta = 25° C)		P _D (Note 1)	150	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

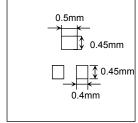
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

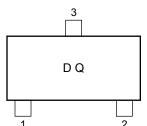
Note 1: Total rating, mounted on FR4 board (25.4 mm \times 25.4 mm \times 1.6 t, Cu Pad: 0.585 mm²)



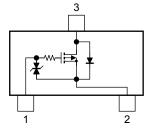
Weight: 0.0015 g(typ.)



Marking



Equivalent Circuit (top view)



Handling Precaution

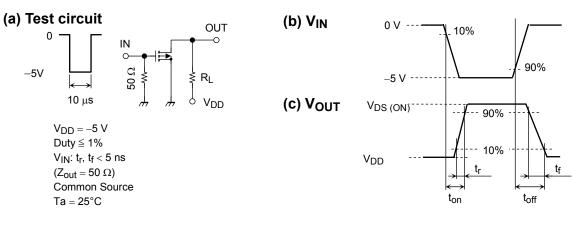
When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Unit: mm

www.DataSheet4U.com Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	MIN.	TYP.	MAX.	UNIT
Gate leakage current		I _{GSS}	$V_{GS}=\pm 16~V,~V_{DS}=0$	_	—	±1	μA
Drain-Source breakdown voltage		V (BR) DSS	$I_D = -0.1 \text{ mA}, V_{GS} = 0$	-30			V
Drain cut-off current		I _{DSS}	$V_{DS} = -30 V, V_{GS} = 0$	_	_	-1	μA
Gate threshold voltage		V _{th}	$V_{DS} = -3 \text{ V}, \text{ I}_{D} = -0.1 \text{ mA}$	-1.1	_	-1.7	V
Forward transfer admittance		Y _{fs}	$V_{DS} = -3 \text{ V}, \text{ I}_{D} = -10 \text{ mA}$	20	_		mS
Drain-Source on-resistance		R _{DS (ON)}	$I_{D} = -10 \text{ mA}, V_{GS} = -4 \text{ V}$	_	8	12	Ω
			$I_D = -1 \text{ mA}, V_{GS} = -2.5 \text{ V}$	_	14	32	
Input capacitance		C _{iss}	V _{DS} = -3 V, V _{GS} = 0, f = 1 MHz	_	9.1		pF
Reverse transfer capacitance		C _{rss}		_	3.5		pF
Output capacitance		C _{oss}		_	8.6		pF
Switching time	Turn-on time	t _{on}	V _{DD} = -5 V, I _D = -10 mA,	—	65		ns
	Turn-off time	t _{off}	$V_{GS} = 0 \sim -5 V$	_	175		

Switching Time Test Circuit



Precaution

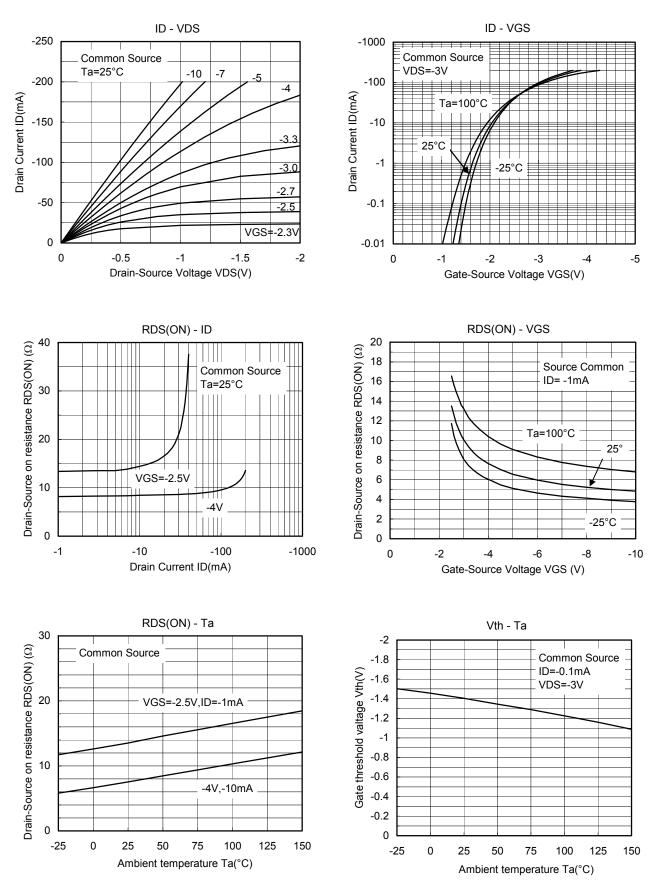
 V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = .100 \mu A$ for this product. For normal switching operation, V_{GS} (on) requires a higher voltage than V_{th} and V_{GS} (off) requires a lower voltage than V_{th} .

(The relationship can be established as follows: V_{GS (off)} < V_{th} < V_{GS (on)})

Please take this into consideration when using the device.

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|Yfs| - ID IDR - VDS 1000 -250 Common Source Common Source VDS= -3V VGS=0V Drain reveres current IDR (mA) Forword transfer admittance |Yfs| (mS) Ta=25°C -200 Ta=25°C 1111 100 -150 -100 10 -50 1 0 -10 -1 -100 -1000 0 0.2 0.4 0.6 0.8 1 1.2 1.4 Drain current ID (mA) Drain-Source voltage VDS (V) t - ID C - VDS 10000 100 Common Source Common Source VDD= -5V VGS=0V toff VGS=0~-5V f=1MHz Switching Time t (ns) Ta=25°C Capacitance C (pF) 1000 Ta=25°C tf 10 ------Ciss 100 ton Coss tr Crss 10 1 -0.1 -1 -10 -100 -0.1 -1 -10 -100 Drain Current ID (mA) Drain-Source voltage VDS (V) PD - Ta 250 mounted on FR4 board Drain power dissipation Pd (mW) 200 (25.4mm×25.4mm×1.6t Cu Pad:0.585mm²) 150 100 50 0 0 20 40 60 80 100 120 140 160

Ambient temperature Ta(°C)



RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
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